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SOME OPTICAL AND ELECTRICAL PROPERTIES
OF SEMICONDUCTING MATERIALS IN THIN FILM FORM

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3

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Contents

	Page
Abstract	i
Introduction	1
Chapter I: Theoretical Background	5
I. 1. Murman's method for determining the optical constants of absorbing thin films deposited on transparent substrates	5
2. The Fermi level for different semiconductors	10
3. Conductivity and mobility in intrinsic semiconductors	15
4. The Hall effect	21
5. The thermoelectric effect	28
6. Surface states	33
Chapter II: Apparatus & Experimental Techniques	36
II.1. Experimental technique for preparation of samples and determination of their thickness.	36
a. The substrate preparation	36
b. The evaporation plant	37
c. The quartz crystal monitor	38

d. The interferometric determination of film thickness	38
2. The techniques applied for the determination of the optical constants of PbSe polycrystalline films	40
a. A brief review of earlier methods	41
b. Methods applied for measurements in the present investigation	41
(i) The measuring of transmittance at normal incidence	41
(ii) The measuring of reflectance at normal incidence	42
3. Experimental techniques for measuring transport properties of PbSe films	43
a. Experimental procedure for measuring PbSe film resistance	44
b. The technique and circuit employed in Hall effect measurements	46
c. The experimental technique used for thermoelectric power measurements	48
4. The method employed for obtaining the X-ray diffraction patterns of PbSe films	51
5. The effect of ambients on the transport properties of the PbSe films	51

a. For resistivity measurements	52
b. For Hall measurements	55
6. The apparatus & experimental technique for surface analysis	57
a. The ESCA system	58
b. The ultra high vacuum chamber	58
c. The analyser chamber	59
d. The X-ray source	62
e. Experimental procedure	63
 Chapter III: The optical properties of polycrystalline PbSe thin films	67
III.1. The spectral distributions of T and R for PbSe thin films	68
2. The determination of the refractive index (n) and the absorption index (k)	68
3. The spectral dispersion of n and k for PbSe films	70
4. Determination of high frequency and static permittivities	71
5. The dependence of the absorption coefficient on the incident frequency	73
6. Discussion	75

Chapter IV: Electrical transport properties of PbSe

thin films	79
IV.1 The resistivity dependence on the deposition rate of PbSe thin films	81
(i) in air	81
(ii) in vacuum	82
2. The ageing effect on the resistivity of PbSe films	83
(i) in air	83
(ii) in vacuum	83
3. Determination of the lattice parameters of PbSe thin films	84
4. The dependence of the crystallite size upon film thickness	87
5. Variation of the X-ray profile with annealing temperature	88
6. The dependence of PbSe film resistivity ρ on the thickness d	89
(i) in air	89
(ii) in vacuum	90
7. PbSe film resistivity dependence on temperature (in air)	91
8. Determination of bulk resistivity ρ_{∞} & mean free path l_0	95

8

9. Film resistivity dependence on temperature under vacuum	98
10. Variation of film resistivity w.r.t. ambient gases, particularly oxygen	100
11. The dependence of the Hall coefficient R_H on the film thickness d	102
12. The variation of the charge density and Hall mobility (μ_H) with the thickness (d)	103
13. The Hall measurements of PbSe films under vacuum	104
a. Variation of the transport properties with time	106
b. The effect of ambients on the Hall measurements	107
14. The variation of the thermoelectric power of PbSe films with temperature	111
15. The variation of the charge carriers density with the film temperature	112
16. Discussion	114
Chapter V: Surface Analysis of PbSe Thin films	126
V.1. Results and observations	127
2. Discussion	134

Conclusions	140
Suggestions for further investigations.	145
References	146
Arabic Summary	

Abstract

Lead selenide thin films of different thicknesses (25-1400 nm.) were deposited onto glass/quartz substrates in vacuum of 10^{-5} Torr as well as 10^{-10} Torr. X-ray diffraction patterns showed that these films have polycrystalline structure.

The optical constants (the refractive index, n , the absorption index, k and the absorption coefficient, α) of the lead selenide films were determined. n and k were independent of the film thickness in the range 30-1000 nm. n showed anomalous dispersion in the region of the fundamental absorption edge ($\sim 3 \mu\text{m}$).

These optical constants were used to determine the high frequency dielectric constant ($\epsilon_{\infty} \approx 20$) and the static permittivity ($\epsilon_0 \approx 195$).

The linear relations of $\alpha^2 = f(h\nu)$ and $\alpha^2 = g(h\nu)$ indicated the existence of both direct and indirect optical transitions, with energy gap values 0.35 and 0.27 eV respectively.

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The electrical transport properties (resistivity, Hall coefficient and thermoelectric power) of lead selenide films were studied in air, in vacuum and in ambient gases. The electrical resistivity dependence on film thickness, measured in air or in vacuum had basically the same behaviour. The Hall measurements showed that the majority of the lead selenide films of thicknesses below 800nm were p-type; and above this thickness the films were usually n-type.

The ambient gases Ar, He and N₂ had no considerable effect on the resistivity and Hall measurements of the films. On the other hand, oxygen had an obvious role in altering the identity of the free charge carriers of the lead selenide films.

The concentration of the charge carriers calculated from the electrical resistivity, Hall and thermoelectric power measurements had the same order of magnitude (10^{17} - 10^{18} cm⁻³).

The interaction between oxygen (as well as the other ambient gases) and lead selenide surfaces was studied through surface scans carried out on the ESCA III

The effect of oxygen on the different Se and Pb photolines was studied in details. Oxygen reactivity appeared more pronounced in the Se-excess samples; being p-type in conduction. The oxide layer formed at exposures of 10^{12} L of oxygen was estimated to be in the monolayer range.

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13

INTRODUCTION

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INTRODUCTION

Semiconductors, which could be chemical elements, metallic oxides, sulfides and selenides, as well as halide and carbide compounds; possess properties which commend them to our most interested attention. In the course of seeking new sources of energy, different semiconductors were used in varistors, thermistors, transistors and photoelectric devices which infiltrated and revolutionized the field of electronics.

They are usually classified according to the nature of the particles which carry current into ionic and electronic semiconductors.

The characteristics of a family of polar semiconductors, consisting of PbS, PbSe and PbTe, have played an important role in providing experimental foundation for theories of various semiconductor phenomena.

These compounds have the cubic rock-salt structure which typifies ionic compounds, and although their chemical behaviour can best be described by regarding them as ionic, their electrical properties bear a greater resemblance to those of group IV elements.

A number of researchers have found that these lead chalcogenides possess a number of interesting features, among which are the following :

- (i) They defy the usual rule that in a series of similar compounds the energy gap falls as the molecular weight increases.
- (ii) Their static dielectric constants are unusually high (178, 206 and 380 for PbS, PbSe and PbTe respectively) as estimated by Burstein et al. [1] among others. Putley [2] indicated that such high values may account for the absence of impurity activation energies even in the purest crystals; and for the absence of ionized impurity scattering at low temperatures.
- (iii) Unlike the majority of semiconductors, the mobility does not fall as the temperature is reduced to the He range. It generally tends to a constant value or may continue to rise slowly. This behaviour is more like that of a metal; showing a constant residual resistance.
- (iv) The mobilities of holes and electrons are of comparable magnitude; unlike those of say, the III-V compounds, which possess very high mobility ratios.